Super-ballistic transport in an open quantum ring

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When the degeneracies of the ring-Hamiltonian are removed by the asymmetric ring-to-electrodes configuration for an open quantum ring (OQR) , the overall junction transmission function exhibits fano-type antiresonance, resulting a net circular current appears within the channel, that is the ring around the degenerate energy levels of the ring-Hamiltonian. We investigate the system size scaling properties of the channel conductance and the overall junction conductance of an OQR. Ballistic transport is the unhindered flow of a charge carrier within a conductor. Here we find beyond-ballistic transport near both the degenerate and non-degenerate eigenenergies of the ring-Hamiltonian, depending on the ring-to-lead configuration. This is a purely OQR phenomenon associated with the quantum interference effect between two counter-propagating electronic waves having nearly equal and opposite momenta. Thus there is no equivalent phenomenon in open quantum junctions with linear channel.

I. INTRODUCTION

The Drude model described the electronic transport process in metals^{[1](#page-7-1)} about 100 years ago. Since then, the nature of electron transport has become the topic of primary interest in a broad area of research and yet fresh mysteries and revelations continue to arise. Three scenarios are seen in the context of the charge carrier transport in low-dimensional systems 2^{-4} 2^{-4} . Ballistic transport occurs in a perfect conductor, where the conductance G is independent of N. Here the charge can flow without any restriction. In an insulator G exponentially decreases with system sizes N, such that $G \sim e^{-\lambda N}$ with $\lambda > 0$. On the other hand, diffusive transport appears in the presence of disorder where G is of the order of $\sim N^{-1}$. The nature of electron transport are studied primarily in iso-lated systems^{[5](#page-8-0)-8}. For example the most famous Ander-son localization^{[9](#page-8-2)[,10](#page-8-3)}, which is a problem of long-standing interest in condensed matter physics^{[11](#page-8-4)}. Here in a tight binding lattice, the system wave function changes from being extended (metal) to exponentially localized (insulator) in the presence an infinitesimal random disorder. On the other hand in an Aubry-André-Harper model, the metal-to-insulator transition arises from the existence of an incommensurate potential of finite strength $12,13$ $12,13$.

In the context of transport, another important variant is the open quantum system where the system of interest is coupled to multiple environments that drive current through the system, and often, for such cases, system size dependence of current/conductance is stud-ied for linear geometries^{[14](#page-8-7)[–16](#page-8-8)}. There are no studies so far that looked at N dependence for OQR. In this paper, we study the system size scaling of electron transport in tight-binding Fermionic open quantum ring which has not been addressed so-far in the literature, to the best of our knowledge.

OQR has unique transport properties compared to linear conductors. In an OQR, the current inside the conductor and the overall junction current can have very different quantitative and qualitative behavior $17-26$ $17-26$ con-

FIG. 1: (Color online). Schematic representation of the tightbinding quantum ring, attached to two semi-infinite electrodes. I_U, I_L , and I_T represent the currents in the upper and lower arms of the ring and the overall junction current, respectively.

trary to the linear conductor, where the current outside the conductor should be equal to the current inside the conductor due to the conservation of charge carriers. Let us consider an OQR as shown in Fig. [1.](#page-0-0) The ring has 6 atomic sites. It is symmetrically connected to the incoming (source) and outgoing (drain) electrodes, i.e., the lengths of the upper and lower arms of the ring are equal. We can write the zero temperature bond current within the ring and the overall junc-tion current as^{[22](#page-8-11)[,27](#page-8-12)-29} $I_{i\rightarrow i+1}(V) = \int J_{i\rightarrow i+1}(E) dE$ and $I_T(V) = \frac{2e}{h} \int T(E) dE$, respectively where e is the electronic charge and h is Planck's constant. $J_{i\rightarrow i+1}(E)$ and $T(E)$ are the transmission functions corresponding to the bond and junction currents, respectively. The junction transmission function $T(E)$ is always a positive quantity with an upper bound of 1 for any type of conductor. Whereas $J_{i\to i+1}(E)$ can be positive or negative with no bound for an OQR. The bond current in a particular arm, say in the upper are the same due to the conservation of current. Therefore, for Fig. [1,](#page-0-0) we can write, $I_{1\to 2} = I_{2\to 3} = I_{3\to 4} = I_U$ (say). Similarly, it is I_L for the lower arm of the ring, such that $I_{4\rightarrow 5} = I_{5\rightarrow 6} = I_{6\rightarrow 1} = I_L$. The overall junction current I_T should be equal to the $I_L - I_U$. Here the positive sign

is assigned to the current moving in the anti-clockwise direction. Conventionally, under non-equilibrium condition, I_U and I_L should flow from the higher chemical potential electrode (source) to the lower chemical potential electrode (drain). So according to our sign convention, I_U should be negative and I_L should be positive. This is true when the ring is symmetrically connected to the leads such that the length of the upper arm and the lower arm of the ring are same. In this case $I_U = -I_L$. But, in an asymmetric ring, an anomalous current may flow against the bias in both arms. We can assign a net circulating current inside the conductor, namely a bias-driven current under such situations. In few works, the circular current is associated with one which flows against the bias $30,31$ $30,31$, whereas few have taken average of the branch currents^{[21](#page-8-16)[,32](#page-8-17)} to define circular current. In this paper, we estimate the system size scaling of the channel conductance within the the conductor and the overall junction conductance of the OQR. To avoid the controversy regarding the definition of the net circular current, here we concentrate on the bond current. Our numerical computations reveal that the system size scaling of the bond conductance and the circular current conductance in both definitions, exhibit the same qualitative trend.

Unlike a chain, a ring Hamiltonian has doubly degenerate energy eigen values associated with the periodic boundary condition $(N + 1 \equiv N)$ of the ring structure, as energy eigenstates having $+k$ and $-k$ momenta, have the same energy. When the ring is connected to the leads in such a way that the lengths of the upper and lower arms of the ring are unequal, the degeneracies get removed. For such an asymmetric ring, the overall junction conductance has two sharp Fano resonance peaks separated by a zero (anti-resonance) at degenerate energies. This is a purely quantum mechanical interference effect. The peaks and dips around the degenerate energies are associated with the poles and zeroes of the conductance and have been studied well in $\text{ref}^{30,31}$ $\text{ref}^{30,31}$ $\text{ref}^{30,31}$ $\text{ref}^{30,31}$. The circular current appears around the degenerate energy states. We find that, though transport and circular currents behave differently with voltage, disorder, etc., they both have the same qualitative dependence on system size. Same as linear conductors, the nature of transport is ballistic except around degenerate energy levels associated with any quantum ring (QR). For a symmetric ring, the conductance increases with N at the band edge. The beyond ballistic growth of conductances with system size can be denoted as super-ballistic transport. We also find super-ballistic transport around anti-resonant states, in an asymmetric ring. The super-ballistic regime can be extended by tuning the ring-to-lead coupling strengths. This anomalous scaling appears due to the fact that QRs with integer multiple system sizes share the same eigenstates around which the conductance has the same peak height whereas the peak width decreases with N. This repetition of eigenstates is purely a QR phenomenon and does not have any linear analogue. In other words, this anomalous scaling can not be found in the bare linear junctions. We also validate our study in the presence of disorder and find a suitable way to tune the superballistic regime by the strength of disorder. The nature

of transport beyond the super-ballistic regime is diffusive.

The rest of the paper is arranged as follows. In Sec. II we discuss the wave-guide approach to calculate the bond and drain currents. In Sec. III, we illustrate all the essential results, and finally, we summarize our findings in Sec. IV.

II. THEORY

The tight-binding Hamiltonian H for the OQR can be written as the sum of sub-Hamiltonians as:

$$
H = H_{\text{Ring}} + H_{\text{Source}} + H_{\text{Drain}} + H_{\text{Tunneling}}.\tag{1}
$$

The forms of sub-Hamiltonians of Eq. [1](#page-1-0) are as follows:

$$
H_{\text{Ring}} = \sum_{i=1} \epsilon_i c_i^{\dagger} c_i + \sum_{i=1} t \left(c_{i+1}^{\dagger} c_i + c_i^{\dagger} c_{i+1} \right), \quad (2)
$$

$$
H_{\text{Source}} = \sum_{n \le -1} \epsilon_0 a_n^{\dagger} a_n + \sum_{n \le -1} t_0 \left(a_n^{\dagger} a_{n-1} + a_{n-1}^{\dagger} a_n \right),\tag{3}
$$

$$
H_{\text{Drain}} = \sum_{n\geq 1} \epsilon_0 b_n^{\dagger} b_n + \sum_{n\geq 1} t_0 \left(b_n^{\dagger} b_{n+1} + b_{n+1}^{\dagger} b_n \right), \quad (4)
$$

$$
H_{\text{Tunneling}} = t_S \left(c_{N_S}^{\dagger} a_{-1} + a_{-1}^{\dagger} c_{N_S} \right)
$$

$$
+ t_D \left(c_{N_D}^{\dagger} b_1 + b_1^{\dagger} c_{N_D} \right). \tag{5}
$$

 ϵ_0, ϵ_i (i = 1, 2, ... N) are the onsite potential of the electrodes and the ring, respectively. t_0 and t are the nearest-neighbor hopping strengths of the electrodes and the ring, respectively. The creation operators $a_n^{\dagger}, b_n^{\dagger}, c_i^{\dagger}$ correspond to the source, drain, and ring, respectively. t_S is the coupling strength of the ring with the source and similarly, t_D stands for the coupling strength with the drain. The electrodes are connected at the N_S -th and N_D -th sites of the ring to the source and drain, re-spectively. For example, in Fig. [1,](#page-0-0) $N_S = 1$ and $N_D = 4$.

The bond and overall junction conductances can be given in terms of $J_{i\to i+1}(E)$ and $T(E)$ as

$$
G_{i \to i+1}(E) = eJ_{i \to i+1}(E)
$$
 (6)

$$
G_T(E) = \left(\frac{2e^2}{h}\right)T(E),\tag{7}
$$

respectively. As $I_T = I_L - I_U$ within a ring junction, therefore $2T(E) = J_L(E) - J_U(E)$. J_U and J_L are the channel transmission functions corresponding to the upper and lower arms, respectively. As we focus on the qualitative nature of electron transport, in this paper we choose $e = h = 1$, for the sake of simplification.

To calculate the transmission functions $J_{i\to i+1}(E)$ and $T(E)$, we adopt wave-guide prescription^{[34](#page-8-18)[,35](#page-8-19)}, where we solve a set of coupled linear equations, generated from

FIG. 2: (Color online). The first row shows the results for a 6-site symmetric ring, while the second row shows the results for the most asymmetric connection. In (a) and (c) channel conductances for the upper and lower arms are plotted as a function of E , while, the variation of the junction conductance with E is displayed in (b) and (d).

the Schrödinger equation $H|\psi\rangle = E|\psi\rangle$, with

$$
|\psi\rangle = \left[\sum_{n \leq -1} A_n a_n^{\dagger} + \sum_{n \geq 1} B_n b_n^{\dagger} + \sum_{i=1} C_i c_i^{\dagger} \right] |0\rangle \qquad (8)
$$

where A_n , B_n and C_i correspond to the electronic wave amplitudes corresponding to the n -th site of the source/drain electrode and at the i -th site of the ring, respectively. In terms of the reflection and transmission coefficients r and τ , the amplitudes A_n and B_n can be written as $A_n = e^{ik(n+1)} + re^{-ik(n+1)}$ and $B_n = \tau e^{ikn}$. k is the wave vector. Here we assume a plane wave occurrence with unit amplitude from the source. Thus these coupled equations looks as follows:

$$
(E - \epsilon_0) A_n = t_0 (A_{n+1} + A_{n-1}), n \le -2,
$$

\n
$$
(E - \epsilon_0) A_{-1} = t_0 A_{-2} + t_S C_{N_S},
$$

\n
$$
(E - \epsilon_0) B_n = t_0 (B_{n+1} + B_{n-1}), n \ge 2,
$$

\n
$$
(E - \epsilon_0) B_1 = t_0 B_2 + t_D C_{N_D},
$$

\n
$$
(E - \epsilon_i) C_i = t (C_{i+1} + C_{i-1}) + t_S \delta_{i, N_S} A_{-1}
$$

\n
$$
+ t_D \delta_{i, N_D} B_1, 1 \le i \le N
$$
\n(9)

Solving Eqs. [9](#page-2-0) we calculate the required transmission functions as $J_{i\rightarrow i+1}(E) = \text{Im} [t C_i^* C_{i+1}]/2\text{sin}(ka)$ and $T(E) = |\tau|^2 = |B_1|^2.$

III. RESULTS AND DISCUSSION

Unless otherwise specified, all onsite energies are set to zero throughout the computations. The hopping parameter inside the ring is set to 1 eV. The source is always connected to the first site of the ring, i.e., $N_S = 1$. The inter-atomic spacing (a) is considered to be $1\AA^{33}$ $1\AA^{33}$ $1\AA^{33}$. The source-to-ring coupling t_S and ring-to-drain coupling t_D are always taken equal and they are denoted as t_C .

FIG. 3: (Color online). In (a) and (b) the channel conductances are plotted with system size N for two different upper and lower arm ratios near the band edge with $E = (2.0 + \Delta \xi)$ eV. For (a) the length ratio is 1 whereas for (b), the ratio is $1/2$. The ring site where the drain is attached, denoted as N_D is marked at the top of (a) and (b). The red, blue, and green color represent $\Delta \xi = 0.0$, 0.0001, and 0.002 , respectively. The dashed line in (a) indicates the system size up to which conductances increase and then decline for $\Delta \xi = 0.0$. For this case, we plot the conductances around the band-edge for various system sizes in (c) where $E = 2$ eV is indicated by dashed line. The hopping parameters for the entire calculation are $t_0 = 1.2 \text{ eV}$ and $t_C = 0.1 \text{ eV}$.

The arrangement of this section is as follows. First, we demonstrate the conductances-energy spectra for symmetric and asymmetric rings to understand the basics of transport in an OQR. Next for both configurations, we study the system size scaling of the conductances at the band edge (i.e., $\pm 2t \text{ eV}$) and within the band edge. In this context, we study the role of the ring-to-lead coupling strength on the scaling. Next, we check the sustainability of the scaling in the presence of disorder. At last, we examine the system size scaling of the total currents.

A. Energy dependence of the conductances

Before studying the system size scaling of the conductance, let us first concentrate on the conductance-energy characteristics. In Fig. [2,](#page-2-1) we plot the bond conductances and overall junction conductance against energy. The hopping parameters for the leads are 2 eV , and the ringto-lead coupling is 0.5 eV. $G_U(E)$ and $G_L(E)$ are the channel conductances for the upper and lower arms of the ring, respectively. The energies associated with the picks and the dips in the spectra correspond to the energy eigenvalues of the ring Hamiltonian (Eq. [2\)](#page-1-1). The energy dispersion relation for the isolated ring is $E = 2t \cos(ka)$, where $k = 2\pi m/Na$. The integer m runs between $-N/2 \leq m < N/2$. Therefore for k and $-k$, the system has the same energy. The non-degenerate energy levels are correspond to $m = 0$ for odd N and $m = -N/2$, 0 for even N. For example, in Fig. [2](#page-2-1) we choose $N = 6$, which implies $m = -3, -2, -1, 0, 1, 2$. Therefore degeneracies appear at $m = \pm 2$ and ± 1 . Whereas the energy

FIG. 4: (Color online). System size scaling of the conductances at the band edge $E = 2$ eV for a symmetric ring for (a) different strength of ring-to-leads coupling strengths (t_C) with $t_0 = 1.2 \text{ eV}$; (b) different choices of t_0 s with t_C fixed at 0.1 eV. The choices for t_{C} at (a) and t_0 for (b) are indicated at the top of the respective figures.

levels corresponding to $m = -3$, that is $E = 2$ eV and $m = 0$ with $E = -2$ eV remain non-degenerate. Therefore, the band edges are non-degenerate and the other eigenenergies of a quantum ring with even N are doubly degenerate.

In Figs. $2(a)$ -(b), for a symmetric ring, we find four resonant peaks. Therefore, the degeneracies are not removed in this case. But for an asymmetric ring, the degeneracies are lifted as we have six resonant peaks in Figs. $2(c)-(d)$. Here the conductances corresponding to degenerate states are split and they are separated by an anti-resonant state (where the conductance is negligible). The anti-resonant states appear at all the degenerate energies of the bare ring. For symmetric ring (Fig. $2(a)$ -(b)), $G_U(E)$ and $G_L(E)$ are exactly equal and opposite to each other, therefore $G_T(E) = 2(G_L(E) - G_U(E)) =$ $4|G_U(E)| = 4|G_L(E)|$. The net circular current within the ring is zero as per definition given in Ref.[30](#page-8-14)[,31](#page-8-15) (as no current flows against the bias) and in Ref.^{[21](#page-8-16)[,32](#page-8-17)} (average bond current is zero) for a symmetric-ring. Whereas, for asymmetric-ring (Fig. $2(c)-(d)$), around degenerate energies, currents flow in same direction as $G_U(E)$ and $G_L(E)$ have same sign. At positive energy, right and left sides of the anti-resonant states, the current in upper and lower arms of the ring flow against the bias, respectively. The phenomena become opposite at negative energy. For nondegenerate states, the currents flow in conventional direction. Therefore, a large circular current can be found around degenerate energy levels, whereas it is negligible around non-degenerate energies.

FIG. 5: (Color online). (a) Scaling of $|G_U|$ with ring-size N at the band-edge $E = 2$ eV for most asymmetric ring-tolead configurations. The black dots represent the numerically calculated values. Using these results, we find the scaling relation between G_U and N, which is shown by a continuous red curve. In the inset, the black dots depict the logarithmic plot of the same data. The red line in the inset represents the fit as $\log G_U = -\log N + \text{constant}$. (b) Conductances around the band-edge for different system sizes. The meaning of the different colors are same as Fig. [3\(](#page-2-2)c). The parameters are the same as in Fig. [3.](#page-2-2)

B. Scaling relation of the conductances at the band-edge

For an OQR, electrons propagate within the energy window around $-2t eV$ to $+2t eV$. We find that apart from the eigen-energies of any QR, the conductance is independent of system size N . This is ballistic transport, which is the mode of transport for a linear conductor. Anomalous transport is observed around the eigen-energies of a QR. Let us first concentrate on the band-edge, which is at $E = \pm 2 eV$ for our choices of parameter values. The conductances for two distinct ring-to-lead arrangements are plotted in Fig. [3.](#page-2-2) Figure $3(a)$ displays the results of a symmetric ring with an upper and lower arm length ratio of 1, whereas the length ratio is $1/2$ for Fig. [3\(](#page-2-2)b). We calculate the conductances at $E = (2 + \Delta \xi)$ eV. The red, blue, and green curves in Figs. [3\(](#page-2-2)a)-(b) correspond to $\Delta \xi = 0$, 0.0001 , and 0.002 , respectively. This is to note that, in a symmetric ring, the magnitude of the G_U and G_L are the same and G_T is 4 times of them. In contrast, the asymmetric ring exhibits distinct magnitudes of the conductances (Fig. [3\(](#page-2-2)b)), but nearly identical qualitative relationships with N . For this reason, we only focus on any one of the conductances in this case. These images demonstrate how the conductances first increase with N at the band edge and subsequently fall at the band edge and very close to the band edge, as seen by the red and

FIG. 6: (Color online). The N dependence of the conductances at $E = (1.0 + \Delta E)$ eV with different ΔE s for most asymmetric ring. The red and blue colors in the first row represent the conductances for the upper and lower arms, respectively. The curves connecting dots represent the conductance of the OQRs with $N \in 6N$. All the calculations are done for $t_C = 0.2$ eV and $t_0 = 2.0 \,\text{eV}$.

blue curves. For larger ξ ($\xi = 0.002$), the conductances decrease with N , as shown by the green curve. Thus the scaling relations at the band edge can be expressed as

$$
G_X(E) \sim N^{\alpha} \quad \forall \quad N < N^C; \\
G_X(E) \sim N^{-\beta} \quad \forall \quad N > N^C,\n \tag{10}
$$

where $X = U$, L, T. α and β are positive numbers. N^C is the length of the ring up to which the conductances increases with N . One can classify the beyond ballistic growth of conductances with N as super-ballistic trans*port.* In contrast near the band edge ($\xi = 0.002$), we conductances scales with N as:

$$
G_X(E) \sim N^{-\gamma} \quad \forall \quad N \tag{11}
$$

where $X = U$, L, T. γ is positive. When $\gamma = 1$, it indicates diffusive transport. If $\gamma > 1$, it is referred to as subdiffusive transport, while the regime where $0 < \gamma < 1$ is termed superdiffusive. To explain the anomalous superballistic transport, we indicate the N_C by a dotted line for $\xi = 0$ in Fig. [3\(](#page-2-2)a). N_C is 800 for this case. Now we calculate the conductances around $E = 2.0 \text{ eV}$ for different system sizes viz, $N = 600, 700, 800, 900,$ and 1000 as shown in Fig. $3(c)$. The vertical dotted line in this figure indicates $E = 2$ eV. The magnitudes of conductance maxima for systems with $N \leq N^C$ are comparable to each other, and then its decrease for larger N. As the spreading of the peaks decreases with N , the maxima positions move from the right to the left of the energy axis. For these reasons, at the band edge, the conductances initially increase with N up to N^C and subsequently decrease. At $\xi = 0.002$, peak maxima drops with N, therefore the conductances decreases with N as shown by the green curves in Fig. [3\(](#page-2-2)a) and (b).

Figure [4](#page-3-0) shows how the system parameters affect N^C . Here for a symmetric-ring, we plot the conductances with N for various strengths of ring-to-leads coupling with fixed t_0 in Fig. [4\(](#page-3-0)a) and different choices of t_0 with fixed ring-to-leads coupling strength t_C in Fig. [4\(](#page-3-0)b). Fig-ure [4\(](#page-3-0)a) shows that N^C becomes higher for weak t_C but it does not depend on t_0 as we can see in Fig. [4\(](#page-3-0)b). Rather we can infer from Fig. [4\(](#page-3-0)b) that for fixed t_C , α and β depend on t_0 . If t_0 is comparable to the ring-hopping (t), α and β becomes larger than 1, resulting superballistic transport for $N < N^C$ and diffusive transport for $N > N^C$. In contrast, the transport behavior is more likely to be ballistic for $t_0 \gg t$.

In Fig. $5(a)$ we plot the system-size scaling for the most asymmetric rings with $N_D = N$ such that the length deference between the upper and lower arms is maximum. For the same parameter values as chosen in Fig [3,](#page-2-2) here we find that the conductance $G_U(E)$ decays with N, at the band edge $E = 2.0 \text{ eV}$. The nature of the transport is diffusive as the scaling relations is:

$$
G_U(E) \sim N^{-1} \quad \forall \quad N. \tag{12}
$$

Additionally, the inset of Fig. [5\(](#page-3-1)a) displays a logarithmic plot, illustrating the conductance scaling as N^-1 . This scaling is robust against the ring-to-lead coupling strength. To illustrate this scaling, we plot the variation of $G_U(E)$ around $E = 2$ eV for different system sizes in Fig. [5\(](#page-3-1)b). In this plot, we observe that the resonant peaks shift towards $E = 2$ eV (indicated by the dashed line) from the right, and the peak height decreases as N increases, leading to a power law decay in conductance with system size. Figure [5](#page-3-1) presents the results for $G_U(E)$, but similar patterns are observed for $G_L(E)$ and $G_T(E)$.

C. Scaling relation of the conductances within the band

As we have already mentioned apart from the energy around the eigenvalues associated with any N , the nature of the transport is ballistic. For a symmetric ring, the nature of the transport is appears to be ballistic at the

FIG. 7: (Color online). (a) $G_U - E$ spectra around $E = 1.0 eV$ for $N = 60$ and 270 for the same parameter values of Fig. [6.](#page-4-0) The energy window $1.0 \le E \le 1.0 + \Delta E$, with $\Delta E = 0.0001$ is shown by the shaded region. (b) $G_U - E$ spectra around $E =$ $1.0 eV$ for different OQRs with $N \in 6\mathbb{N}$ the same parameter values of Fig. [6.](#page-4-0)

eigen-energies within the edges. However, we see super-ballistic transport as given in Eq. [10,](#page-4-1) where α and β are greater than but near 1, if we only take into account the rings which have that eigen-energy. In an asymmetric ring with commensurate upper and lower arms ratio, the degeneracy may or may not be broken. Consequently, we find ballistic transport at any eigen-energy in this scenario.

Now we focus on the most-asymmetric junctions. Fig. [6](#page-4-0) we plot the conductances as a function of N , at and around an energy corresponding to a degenerate energy level. The channel conductances are plotted in the first row and the over all junction conductance is shown in the second row. The results are calculated for $E = (2.0 + \Delta E)$ eV with $\Delta E = 0.0$ for Fig. [6\(](#page-4-0)a) and (e), 0.0001 for Fig. $6(b)$ and (f), 0.005 for Fig. $6(c)$ and (g) , and 0.1 for Fig. $6(d)$ and (h) . As we have already discussed, for $N = 6$, the QR has degeneracy at $E = 1$ eV. This implies, for all the rings having number of sites $N \in 6\mathbb{N}$, have common degenerate energy levels at $E = \pm 1$ eV. Here we find that, the qualitative natures of transport are same for bond currents and junction current. At $E = 1.0$ eV, the nature of transport is ballistic, as the conductances are independent of N as we can see in Figs. [6\(](#page-4-0)a) and (e). As for the systems with $N \in 6\mathbb{N}$, the conductances are vanishing small due to anti-resonance at $E = 1$ eV, the peaks in the Figs. [6\(](#page-4-0)a)-(e), are associated with rings with sizes $N \notin 6\mathbb{N}$. As for these systems, 1 eV is not an eigen-energy hence the overall transport becomes ballistic. In Fig. [6\(](#page-4-0)b) and (f), we focus at the energy $E = (1 + \Delta E)$ eV where $\Delta E = 0.0001$ eV. Here we find that, up to certain N (say N_U^C for $G_U(E)$, N_L^C for $G_U(E)$ and N_T^C for $G_T(E)$), the conductance increases

FIG. 8: (Color online). (a) Variation of ΔE^N with ring size N around $E = 1.0 \text{ eV}$. The meaning black dots and red curve are the same as Fig. [6.](#page-4-0) In the inset, the black dots illustrate the logarithmic plot of the same data. The red line in the inset shows the fit as $\log \Delta E^N = -\log N + \text{ constant}$. Here we choose $t_C = 0.1$ eV and $t_0 = 1$ eV. (b) Resonant peaks of $J_U(E)$ around degenerate energy $E_n = 1.0 \text{ eV}$ and $N = 30$ for different ring-to-lead coupling strengths.

with N and beyond that, they decline. The peaks are contributed by the QRs having $N \in 6\mathbb{N}$ as indicated by the curves connecting dots. The super-ballistic scaling relation is found to satisfy an power series of N , such that

$$
G_X = a_0 + a_1 N^1 + a_2 N^2 + a_3 N^3 \dots,
$$
 (13)

 $X = U, L, T. a_i s (i = 0, 1, 2, 3, ...)$ are coefficient. a_i s with $i > 2$ become smaller and smaller with $a_{i+1}/a_i \sim 10^{-2}$. For $N > N^C$, the systems have diffusive transport. As our chosen energy is around the degenerate energy levels for $N \in 6\mathbb{N}$, the bond conductances for both the arms have same sign and almost equal magnitude as we already discussed in Fig. [2\(](#page-2-1)b). The conductances for other Ns become very small compared to the conductance for OQRs with $N \in 6\mathbb{N}$ at 1 eV. For $\Delta E = 0.005 \,\text{eV}$ (Fig. [6\(](#page-4-0)c) and (g)), we find diffusive transport. For larger values of ΔE (i.e, $\Delta E = 0.1$ eV), we find ballistic transport as shown in Fig. [6\(](#page-4-0)d) and (h) where the conductances are mostly dominated by the ring sizes $N \notin 6N$ $N \notin 6N$ $N \notin 6N$. The results shown in Fig. 6 are true for any energy corresponding to degenerate eigen energy of an isolated ring of size N . For example, for $N = 8$, we have $m = -4, -3, -2, -1, 0, 1, 2, 3$, where degeneracies are corresponds to $m = \pm 1, \pm 2, \pm 3$. Therefore, we can find the super-ballistic transport very close to the energies $E = 2t \cos[2\pi(\pm \frac{3}{8})], 2t \cos[2\pi(\pm \frac{2}{8})], 2t \cos[2\pi(\pm \frac{1}{8})]$ eVs as these are degenerate energy levels of QRs with $N \in$ 8N.

There exist further asymmetric configurations with $N_D = N - 1$, $N - 2$, ... that exhibit similar anoma-

FIG. 9: (Color online). Variation of G_U with ring size N in the presence AA modulation of the onsite potential with different strengths of disorder. Here we choose the most asymmetry in the ring-to-lead configuration with $t_C = 0.2$ eV and $t_0 = 2$ eV. In (a), the disorder strength is 0. In this case, we set the energy near a degenerate energy level with $E = (1.0 + 0.0002)$ eV. In (b) - (c), w is non-zero and the energy is set at 1 eV.

lous scaling.

D. To find ΔE

The choice of ΔE s is very important to find superballistic transport in an asymmetric-ring. Let us first understand the role of ΔE to have the anomalous system size scaling of $G_U(E)$. We select two values of N from Fig. [6\(](#page-4-0)b), such that for first one $G_U(E)$ is increasing with N and second one where it is decreasing with N. For example, we choose $N = 60$ and 270, respectively as these ring sizes are integer multiple of 6. We plot the $G_U(E)$ around $E = 1.0$ eV for $N = 60$ and 270 in Fig. [7\(](#page-5-0)a). The OQRs with $N \in 6\mathbb{N}$, have degeneracy around 1 eV that is splitted due to asymmetric ring-to-lead connection. We only concentrate at the right side of $E = 1$ eV as we choose $E = 1 + \Delta E$ (ΔE is positive) for our calculations of Fig. [6.](#page-4-0) Let us define an quantity ΔE^N , such that $1 + \Delta E^N$ we have the maximum of $G_U(E)$ at the the right side of $E = 1$ eV for a particular N. In other words, ΔE^N that is the splitting of a degenerate energy levels due to asymmetric ring-to-lead configuration from the degenerate energy of an isolated ring. From Fig. [7\(](#page-5-0)a), we find that $1 + \Delta E < 1 + \Delta E^{60}$ but $1 + \Delta E >$ $1 + \Delta E^{270}$. As around $E = 1$ eV, all resonant peaks of $G_U(E)$ corresponding to different N with $N \in 6\mathbb{N}$, have almost same magnitude (as shown in Fig. [7\(](#page-5-0)b)), therefore we can conclude that, as long as our chosen ΔE is less than ΔE^N , $G_U(E)$ increases with N (as we see for $N = 60$). But when ΔE becomes greater than ΔE^N , $G_U(E)$ decreases with N (as for $N = 270$). For $N = N_U^C$, ΔE becomes equal to ΔE^N . In a similar way, we can explain the transport behavior of $G_L(E)$ and $G_T(E)$ up to $N = N_L^C$ and $N = N_T^C$, respectively. This is to note that as the splitting of the resonant peaks at the left and right sides of the anti-resonant state are

FIG. 10: (Color online). Variation of current $|I_U|$ with N for different ring-to-leads coupling strengths t_C . The magnitudes of t_{C} s are indicated on the top. m is 1, 6, and 15 for $t_{C} = 0.1$, 0.25 , and 0.4 eV, respectively. The current is calculated for 1 mV and the Fermi energy is set at 1 eV.

not same, ΔE^N will be different for both the sides.

E. Roll of N and t_C on ΔE^N

From our so far discussion, we find that to have superballistic scaling behavior, we need to set the Fermi energy at $E_m \pm \Delta E$, where E_m is the generate energy corresponding to the isolated ring and ΔE is less than ΔE^N . The splitting of a degenerate energy level due to asymmetric ring-to-lead configuration from the degenerate energy of an isolated ring that is the ΔE^N is very small (of the order of few meV or less) and it decreases with system size N as $1/N$ as we can see in Fig. [8\(](#page-5-1)a) and in the inset. Now we concentrate to make the ΔE^N reasonable enough for experimental observation. One of the possible way out to make the larger splitting is by controlling the ring-to-lead coupling. In Fig. [8\(](#page-5-1)b) we plot the $G_U(E)$ around an degenerate energy (say, 1 eV for $N = 30$) for different values of ring-to-lead coupling strengths $(t_S = t_D = t_C,$ say). As we can see here, ΔE^N increases with t_C . Therefore we can choose a higher ΔE for larger t_C . But with t_C , the peak heights of the $G_U(E)$ decrease with t_C . As a result, for a fixed ΔE with larger t_C , the corresponding super-ballistic behavior becomes a small scale phenomena $(N_X^C s, X = U, L, T$ become smaller). So we can choose a moderate t_C to have the super-ballistic scaling relation for a reasonable ΔE . From our study we find that, if the degeneracy get removed my the asymmetric ring-to-lead configurations, the peak heights and ΔE^N are independent of the positions of leads. Hence the estimated ΔE^N does not depend on specific ring-toleads connection. This also indicates the robustness of our study.

Same way, we can fix t_C for $G_L(E)$ and $G_T(E)$.

F. Effect of disorder

We now incorporate the effects of disorder into the model in an attempt to make it more realistic. Here, we examine the Aubry-André model $36-40$ $36-40$ of correlated disorder where the impurities in the ring are included by

choosing the onsite energies of the ring in the form of $\epsilon_i = w\cos(2\pi bi)$, where w is the impurity strength and b is an irrational number. We set $b = (1 + \sqrt{5})/2$. The ordered ring is represented by $w = 0$. To investigate the effect of disorder, one can also look at random site energies rather than "correlated" disorder. However, in that scenario, we would take the average over a huge number of different disordered configurations. To avoid it, we will disregard random distribution in this instance and no physical picture will be altered. We have illustrated the impact of the disorder on the system size variations of the conductance in Fig. [9.](#page-6-0) We only focus on the most asymmetric ring-to-lead configuration. Figure $9(a)$ shows an ordered instance. In this case, we set the energy at $(1 + \Delta E)$ eV with $\Delta E = 0.0002$ eV. As 1 eV is a degenerate energy level for rings with $N \in 6\mathbb{N}$, we find superballistic transport (up to N^C , say) near degeneracy for ordered-ring. Figs. [9\(](#page-6-0)b), (c), and (d) represent disordered case with $w = 0.0001, 0.0002,$ and 0.0003 , respectively. Since the conductance is not zero at $E = 1$ eV in the presence of non-zero disorder, we set the energy precisely at $E = 1$ eV in these situations. We find that, in the presence of a small disorder such that $w < \Delta E$ or $w \sim \Delta E$, the super-ballistic behavior remains intact. In fact, in the presence of a small disorder, N^C becomes larger as the disorder creates more asymmetry in the ring which aids in the degeneracy breaking. For $w > \Delta E$ (Fig. [9\(](#page-6-0)d)), super-ballistic behavior becomes short range (Fig. [9\(](#page-6-0)d)). It is therefore possible to tune the length over which we get super-ballistic transport by the strength of the disorder.

G. Total current

We now investigate whether the total currents exhibit the anomalous scaling with system size. To calculate the current we integrate the corresponding transmission functions (as stated in the Sec. I) over the energy window. As the peak and dip heights are unequal, we can set the Fermi energy exactly at the degenerate energy level and integrate a small energy window to study the scaling relationships. The choice of voltage V should be less than, $e\Delta E^N$. In Fig. [10,](#page-6-1) we plot the $|I_U|$ vs N at $t_C = 0.1, 0.25,$ and 0.4 eV shown by red, green, and blue colors. $|I_U|$ is multiplied by 1, 6, and 15, for $t_C = 0.1$, 0.25 , and 0.4 eV, respectively for the better presentation. The currents are calculated for 1 mV. We set the Fermi energy correspond to the degenerate energy for $N \in 6\mathbb{N}$. Anomalous growth of current with system size N is also seen here. For higher ring-to-lead coupling strength, the growth is found till larger N or this phenomenon becomes long-range.

IV. CONCLUSION

We have studied the system size scaling of the conductances within the conductor and the over all junction conductance considering an open quantum ring for the first time in the literature, to the best of our knowledge. Unlike, a linear chain, a QR has the same energyeigen values with integer multiple system sizes. Around these eigenvalues, conductances have the maxima with the same height but the peak widths decrease ring-size N. As a result, anomalous scalings have been found in an OQR at and around energy-eigen values of QRs. Below we summarize our findings.

• Though channel conductance and junction conductance are very different but they exhibit similar qualitative dependence on ring size N. Similar to linear conductors, ballistic transport has been found throughout the conducting energy window except the eigen-energies corresponding to any QR.

• Anomalous beyond ballistic, namely super-ballistic transport is observed at the band edges of a symmetric junction as any QRs with even ring sizes have the same non-degenerate band edges. The nature of transport beyond the super-ballistic regime is diffusive. The super-ballistic regime can be tuned by ring-to-lead coupling strength.

• Within the band edge, all the eigen-energies are doubly degenerate. In an asymmetric ring, the degeneracy gets broken. As a result, there appear two peaks around the energy-eigen value where the conductances become zero. Super-ballistic transport is found close to these degenerate energy levels under asymmetric ring-to-lead configurations.

• As disorder creates more asymmetry to the junction, the super-ballistic transport sustains up to larger system size in the presence of small disorder compared to the order rings. In fact it is possible to manipulate the super-ballistic regime by the strength of disorder. The anomalous scaling remains intact in the circular and the junction currents.

As the origin of anomalous scaling is related to degeneracies of QRs due to periodic boundary condition, thus this does not have any analogue in OQ junctions with linear channels. Our qualitative study will open up interest for the further investigation of open quantum rings in the presence of various conditions like magnetic-field, spin-orbit interaction, dephasing etc..

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